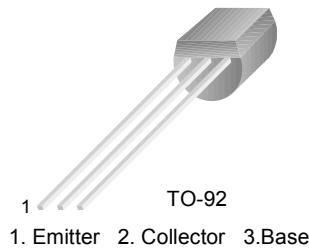


# FJN3303

## High Voltage Fast-Switching NPN Power Transistor

- High Voltage Capability
- High Switching Speed
- Suitable for Electronic Ballast and Charger



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	700	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	9	V
I <sub>C</sub>	Collector Current (DC)	1.5	A
I <sub>CP</sub>	Collector Current (Pulse) *	3	A
I <sub>B</sub>	Base Current (DC)	0.75	A
I <sub>BP</sub>	Base Current (Pulse) *	1.5	A
P <sub>C</sub>	Collector Power Dissipation (T <sub>C</sub> = 25°C)	1.1	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

\* Pulse Test: Pulse Width = 5ms, Duty Cycle ≤ 10%

**Electrical Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = 500\mu\text{A}, I_E = 0$	700			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	400			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = 500\mu\text{A}, I_C = 0$	9			V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = 700\text{V}, I_E = 0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 9\text{V}, I_C = 0$			10	$\mu\text{A}$
$h_{FE1}$ $h_{FE2}$	DC Current Gain	$V_{CE} = 2\text{V}, I_C = 0.5\text{A}$ $V_{CE} = 2\text{V}, I_C = 1.0\text{A}$	14 5		23	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$ $I_C = 1.0\text{A}, I_B = 0.25\text{A}$ $I_C = 1.5\text{A}, I_B = 0.5\text{A}$			0.5 1.0 3.0	V V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$ $I_C = 1.0\text{A}, I_B = 0.25\text{A}$			1.0 1.2	V V
$f_T$	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.1\text{A}$	4			MHz
$t_{ON}$	Turn On Time	$V_{CC} = 125\text{V}, I_C = 1\text{A}$ $I_{B1} = -I_{B2} = -0.2\text{A}$ $R_L = 125\Omega$			1.1	$\mu\text{s}$
$t_{STG}$	Storage Time				4.0	$\mu\text{s}$
$t_F$	Fall Time				0.7	$\mu\text{s}$

**Thermal Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Thermal Resistance Junction-Case	48	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	125	$^\circ\text{C/W}$

## Typical Performance Characteristics

Figure 1. Static Characteristic

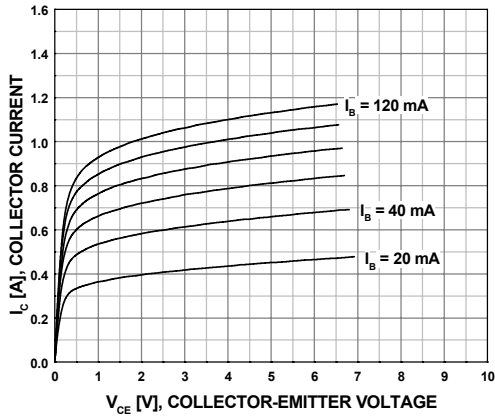


Figure 2. DC Current Gain

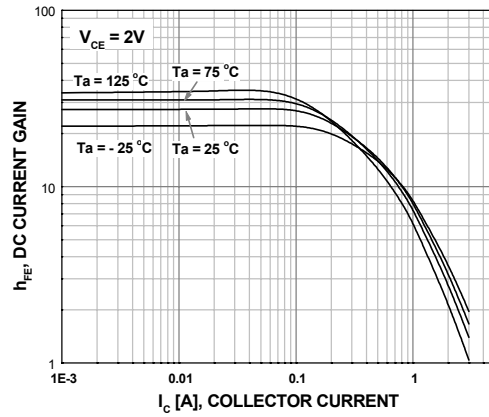


Figure 3. Collector-Emitter Saturation Voltage

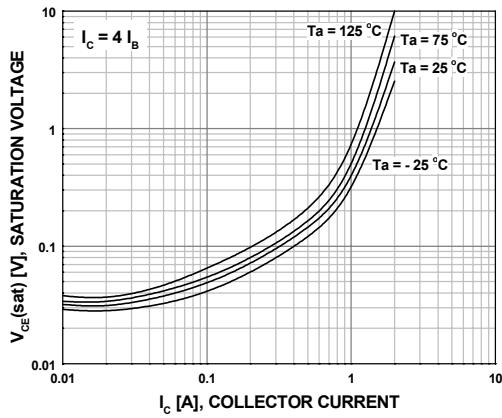


Figure 4. Base-Emitter Saturation Voltage

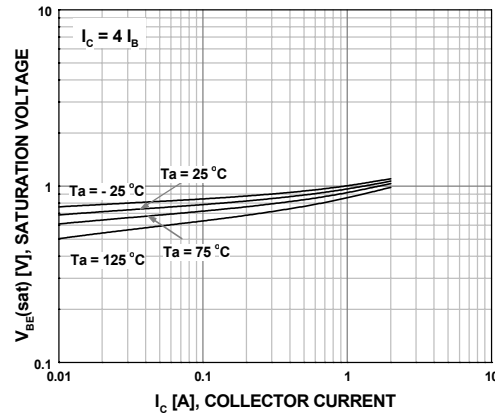


Figure 5. Resistive Load Switching Time

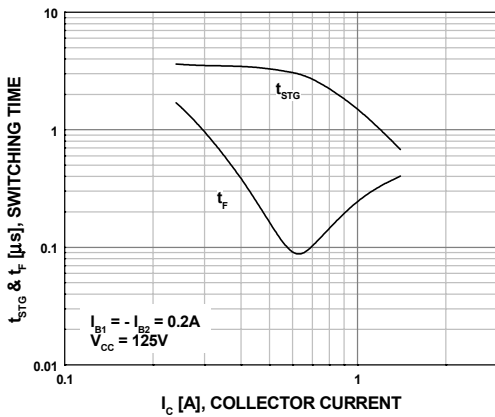
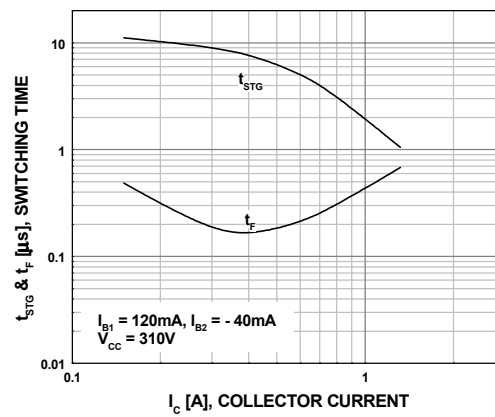
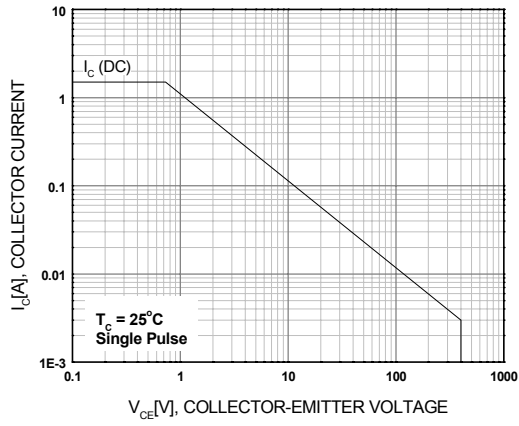


Figure 6. Resistive Load Switching Time

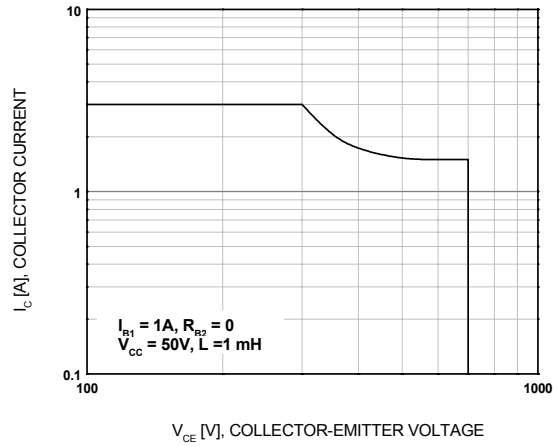


**Typical Performance Characteristics** (Continued)

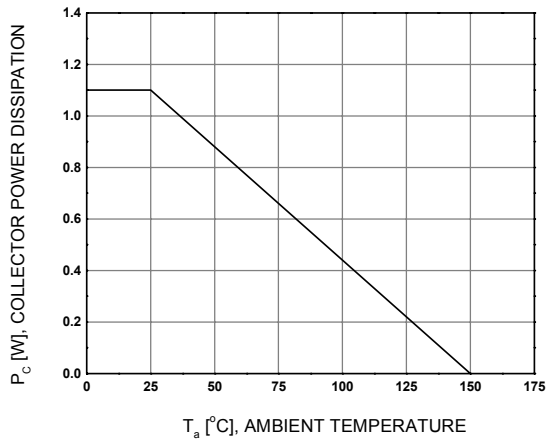
**Figure 7. Forward Biased Safe Operating Area**



**Figure 8. Reverse Biased Safe Operating Area**

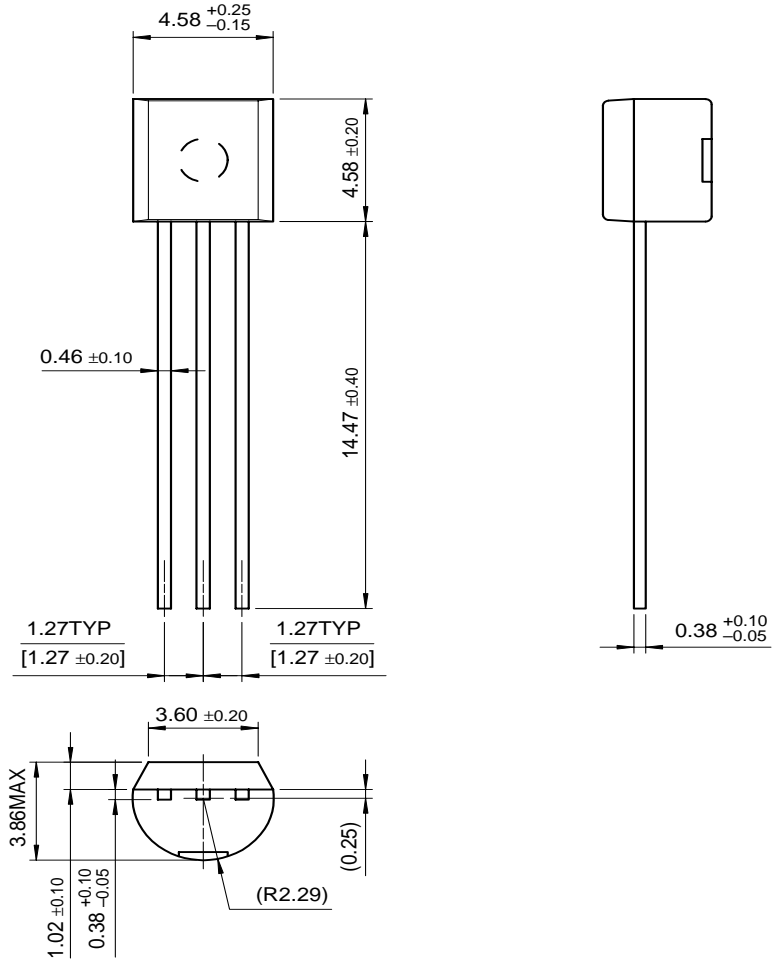


**Figure 9. Power Derating**



Mechanical Dimensions

TO-92



Dimensions in Millimeters

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FACT™	ImpliedDisconnect™	OCX™	RapidConfigure™	TruTranslation™
FACT Quiet Series™		OCXPro™	RapidConnect™	UHC™
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The Power Franchise <sup>®</sup>		OPTOPLANAR™	SILENT SWITCHER <sup>®</sup>	UniFET™
Programmable Active Droop™		PACMAN™	SMART START™	VCX™

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